

September 2009

4N25M, 4N26M, 4N27M, 4N28M, 4N35M, 4N36M, 4N37M, H11A1M, H11A2M, H11A3M, H11A4M, H11A5M **General Purpose 6-Pin Phototransistor Optocouplers**

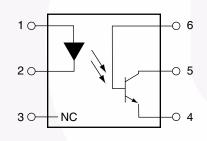
Features

- UL recognized (File # E90700, Volume 2)
- VDE recognized (File # 102497)
 - Add option V (e.g., 4N25VM)

Applications

- Power supply regulators
- Digital logic inputs
- Microprocessor inputs

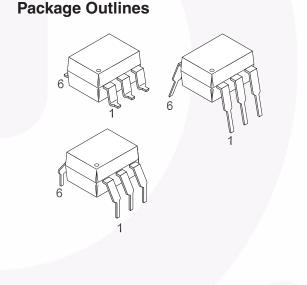
Schematic



PIN 1. ANODE 2. CATHODE **3. NO CONNECTION** 4. EMITTER 5. COLLECTOR 6. BASE

Description

The general purpose optocouplers consist of a gallium arsenide infrared emitting diode driving a silicon phototransistor in a 6-pin dual in-line package.



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Absolute Maximum Ratings ($T_A = 25^{\circ}C$ unless otherwise specified)

Stresses exceeding the absolute maximum ratings may damage the device. The device may not function or be operable above the recommended operating conditions and stressing the parts to these levels is not recommended. In addition, extended exposure to stresses above the recommended operating conditions may affect device reliability. The absolute maximum ratings are stress ratings only.

Symbol	Parameter	Value	Units
TOTAL DEV	ICE		
T _{STG}	Storage Temperature	-40 to +150	°C
T _{OPR}	Operating Temperature	-40 to +100	°C
T _{SOL}	Wave solder temperature (see page 8 for reflow solder profile)	260 for 10 sec	°C
PD	Total Device Power Dissipation @ T _A = 25°C	250	mW
	Derate above 25°C	2.94	
EMITTER			1
۱ _F	DC/Average Forward Input Current	60	mA
V _R	Reverse Input Voltage	6	V
l _F (pk)	Forward Current – Peak (300µs, 2% Duty Cycle)	3	A
PD	LED Power Dissipation @ T _A = 25°C	120	mW
	Derate above 25°C	1.41	mW/°C
DETECTOR			
V _{CEO}	Collector-Emitter Voltage	30	V
V _{CBO}	Collector-Base Voltage	70	V
V _{ECO}	Emitter-Collector Voltage	7	V
PD	Detector Power Dissipation @ $T_A = 25^{\circ}C$ 150		mW
	Derate above 25°C	1.76	mW/°C

Electrical Characteristics (T_A = 25°C unless otherwise specified)

Individual Component Characteristics

Symbol	Parameter	Parameter Test Conditions		Тур.*	Max.	Unit
EMITTER						
V _F	Input Forward Voltage	I _F = 10mA		1.18	1.50	V
I _R	Reverse Leakage Current	V _R = 6.0V		0.001	10	μA
DETECTOR				•		
BV _{CEO}	Collector-Emitter Breakdown Voltage	I _C = 1.0mA, I _F = 0	30	100		V
BV _{CBO}	Collector-Base Breakdown Voltage	$I_{\rm C} = 100 \mu {\rm A}, I_{\rm F} = 0$	70	120		V
BV _{ECO}	Emitter-Collector Breakdown Voltage	I _E = 100μA, I _F = 0	7	10		V
I _{CEO}	Collector-Emitter Dark Current	$V_{CE} = 10V, I_F = 0$		1	50	nA
I _{CBO}	Collector-Base Dark Current	V _{CB} = 10V			20	nA
C _{CE}	Capacitance	$V_{CE} = 0V$, f = 1 MHz		8		pF

Isolation Characteristics

Symbol	Characteristic	Test Conditions	Min.	Тур.*	Max.	Units
V _{ISO}	Input-Output Isolation Voltage	f = 60Hz, t = 1 sec	7500			Vac(pk)
R _{ISO}	Isolation Resistance	V _{I-O} = 500 VDC	10 ¹¹			Ω
C _{ISO}	Isolation Capacitance	V _{I-O} = &, f = 1MHz		0.2	2	pF

*Typical values at T_A = 25°C

Electrical Characteristics (Continued) ($T_A = 25^{\circ}C$ unless otherwise specified)

Transfer Characteristics

Symbol	Parameter	Test Conditions	Device	Min.	Typ.*	Max.	Unit
DC CHARA	CTERISTICS						
CTR	Current Transfer Ratio, Collector to Emitter	I _F = 10mA, V _{CE} = 10V	4N35M, 4N36M, 4N37M	100			%
			H11A1M	50			1
			H11A5M	30			1
			4N25M, 4N26M H11A2M, H11A3M	20			
			4N27M, 4N28M H11A4M	10			
		$I_F = 10mA$, $V_{CE} = 10V$, $T_A = -55^{\circ}C$	4N35M, 4N36M, 4N37M	40			
		$I_F = 10mA, V_{CE} = 10V,$ $T_A = +100^{\circ}C$	4N35M, 4N36M, 4N37M	40			
V _{CE} (SAT)	Collector-Emitter Saturation Voltage	$I_{\rm C} = 2$ mA, $I_{\rm F} = 50$ mA	4N25M, 4N26M, 4N27M, 4N28M,			0.5	V
		I _C = 0.5mA, I _F = 10mA	4N35M, 4N36M, 4N37M			0.3	
			H11A1M, H11A2M, H11A3M, H11A4M, H11A5M			0.4	
AC CHARA	CTERISTICS				1		
T _{ON}	Non-Saturated Turn-on Time	$I_{F} = 10mA, V_{CC} = 10V,$ $R_{L} = 100\Omega$ (Fig. 11)	4N25M, 4N26M, 4N27M, 4N28M, H11A1M, H11A2M, H11A3M, H11A4, H11A5M		2		μs
		$I_{C} = 2mA, V_{CC} = 10V,$ $R_{L} = 100\Omega$ (Fig. 11)	4N35M, 4N36M, 4N37M		2	10	μs
T _{OFF}	Turn-off Time	$I_{F} = 10mA, V_{CC} = 10V,$ $R_{L} = 100\Omega$ (Fig. 11)	4N25M, 4N26M, 4N27M, 4N28M, H11A1M, H11A2M, H11A3M, H11A4M, H11A5M		2		μs
		$I_{C} = 2mA, V_{CC} = 10V,$ $R_{L} = 100\Omega$ (Fig. 11)	4N35M, 4N36M, 4N37M		2	10	

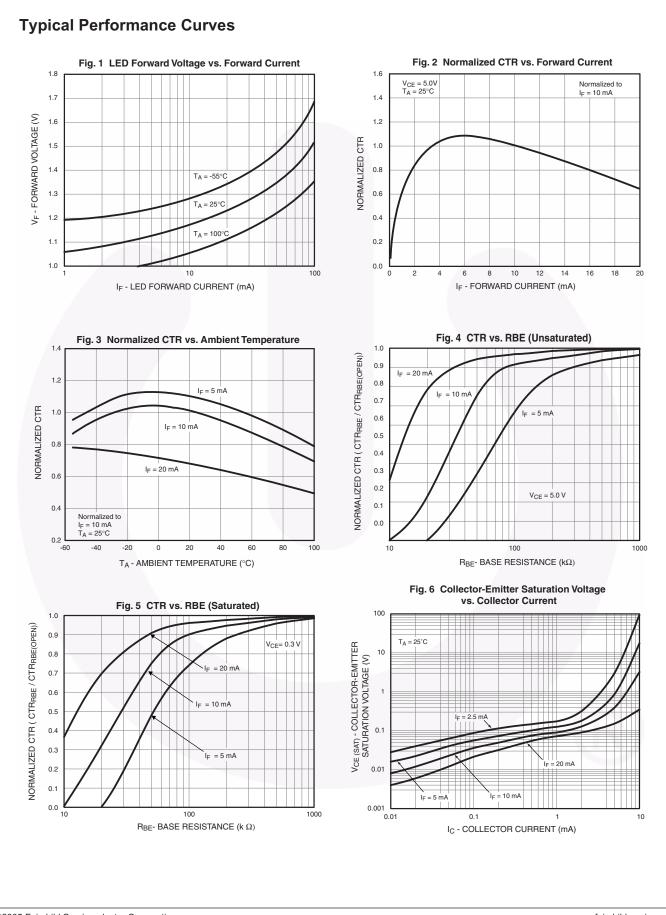
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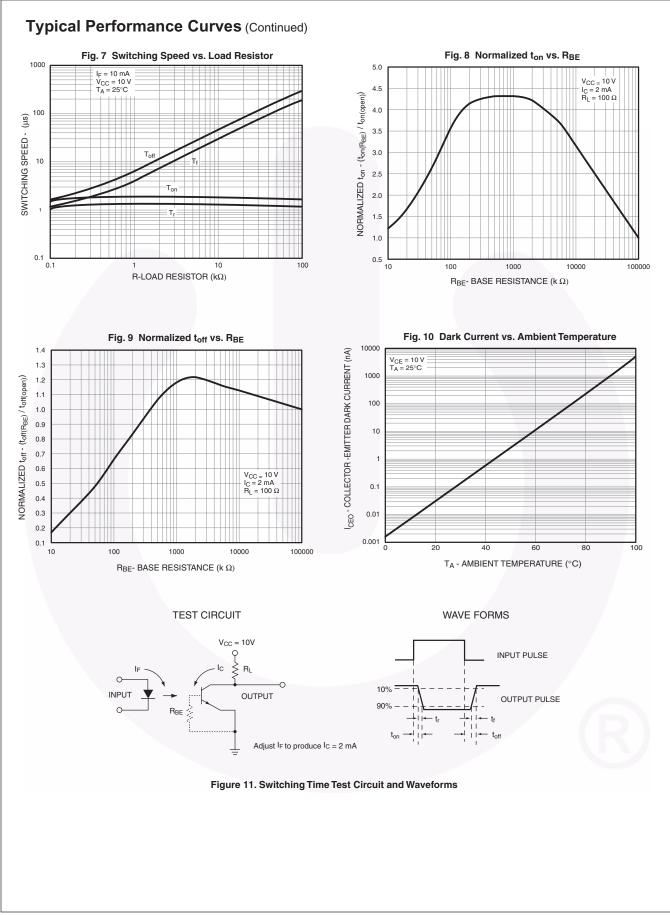
Safety and Insulation Ratings

As per IEC 60747-5-2, this optocoupler is suitable for "safe electrical insulation" only within the safety limit data. Compliance with the safety ratings shall be ensured by means of protective circuits.

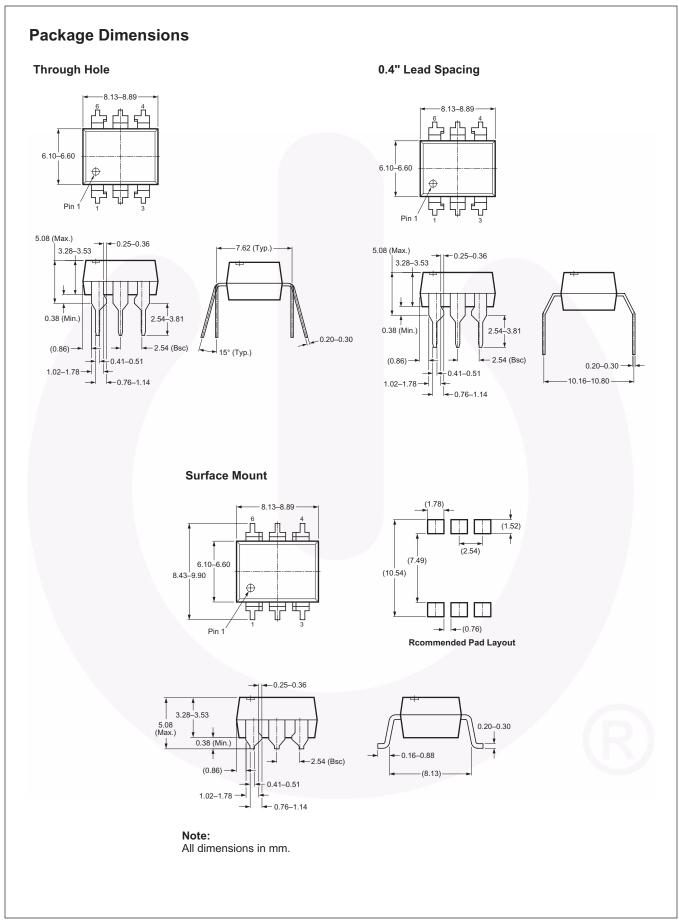
Symbol	Parameter	Min.	Тур.	Max.	Unit
	Installation Classifications per DIN VDE 0110/1.89 Table 1				
	For Rated Main Voltage < 150Vrms		I-IV		
	For Rated Main voltage < 300Vrms		I-IV		
	Climatic Classification		55/100/21		
	Pollution Degree (DIN VDE 0110/1.89)		2		
CTI	Comparative Tracking Index	175			
V _{PR}	Input to Output Test Voltage, Method b, $V_{IORM} \times 1.875 = V_{PR}$, 100% Production Test with tm = 1 sec, Partial Discharge < 5pC	1594			V _{peak}
	Input to Output Test Voltage, Method a, $V_{IORM} \times 1.5 = V_{PR}$, Type and Sample Test with tm = 60 sec, Partial Discharge < 5pC	1275			V _{peak}
V _{IORM}	Max. Working Insulation Voltage	850			V _{peak}
V _{IOTM}	Highest Allowable Over Voltage	6000			V _{peak}
	External Creepage	7			mm
	External Clearance	7			mm
	Insulation Thickness	0.5			mm
RIO	Insulation Resistance at Ts, V_{IO} = 500V	10 ⁹			Ω



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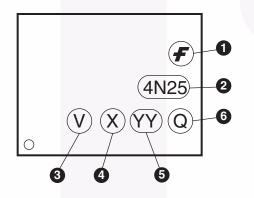


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Ordering Information

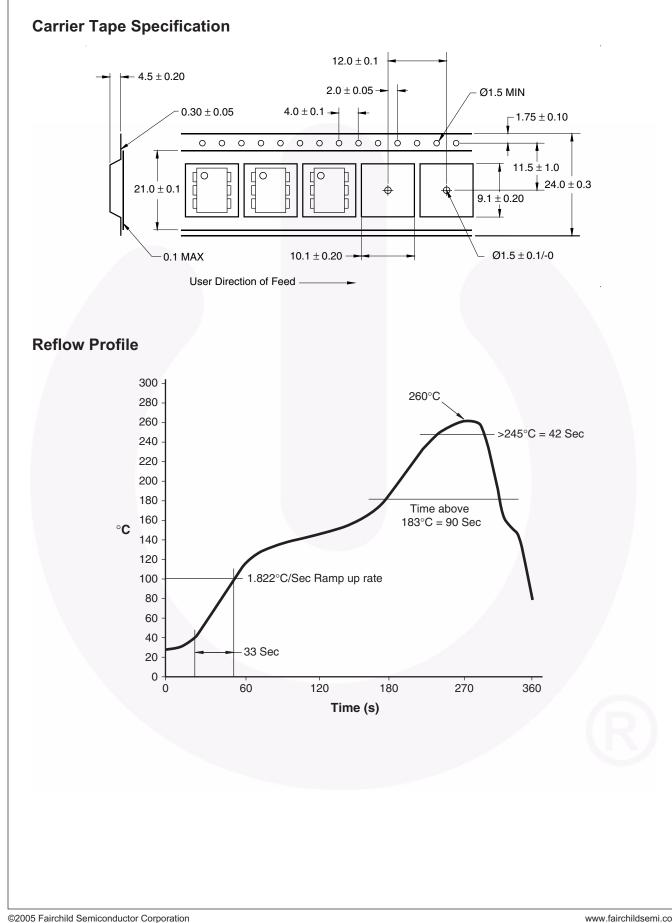
Option	Order Entry Identifier (Example)	Description	
No option	4N25M	Standard Through Hole Device	
S	4N25SM	Surface Mount Lead Bend	
SR2	4N25SR2M	Surface Mount; Tape and Reel	
Т	4N25TM	0.4" Lead Spacing	
V	4N25VM	VDE 0884	
TV	4N25TVM	VDE 0884, 0.4" Lead Spacing	
SV	4N25SVM	VDE 0884, Surface Mount	
SR2V	4N25SR2VM	SR2VM VDE 0884, Surface Mount, Tape and Reel	

Marking Information

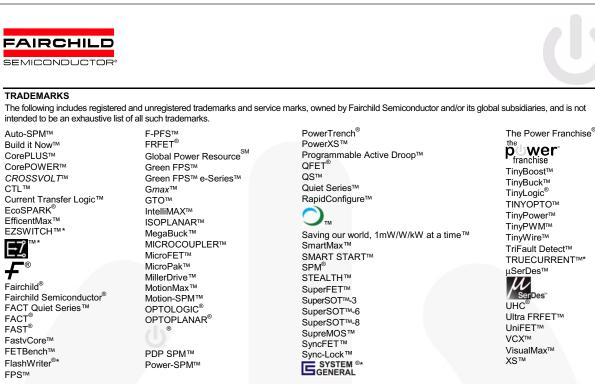


Definitions				
1	Fairchild logo			
2	Device number			
3	VDE mark (Note: Only appears on parts ordered with VDE option – See order entry table)			
4	One digit year code, e.g., '7'			
5	Two digit work week ranging from '01' to '53'			
6	Assembly package code			

*Note – Parts that do not have the 'V' option (see definition 3 above) that are marked with date code '325' or earlier are marked in portrait format.



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Definition of Terms					
Datasheet Identification	Product Status	Definition			
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Preliminary	First Production	Datasheet contains preliminary data; supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve design.			
No Identification Needed	Full Production	Datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve the design.			
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